

ROHS V

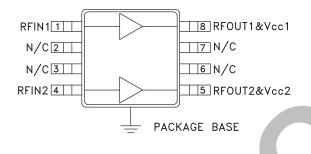
SiGe HBT DUAL CHANNEL GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Typical Applications

The HMC469MS8G /HMC469MS8GE is a dual RF/IF gain block & LO or PA driver:

- Cellular / PCS / 3G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment

Functional Diagram



Features

P1dB Output Power: +18 dBm Gain: 15 dB Output IP3: +34 dBm Supply (Vs): +5V to +12V 14.9 mm² Ultra Small 8 Lead MSOP

General Description

The HMC469MS8G & HMC469MS8GE are SiGe HBT Dual Channel Gain Block MMIC SMT amplifiers covering DC to 5 GHz. These versatile products contain two gain blocks, packaged in a single 8 lead plastic MSOP, for use as either separate cascadable 50 Ohm RF/IF gain stages, LO or PA drivers or with both amplifiers combined utilizing external 90° hybrids to create a high linearity driver amplifier. Each amplifier in the HMC469MS8G(E) offers 15 dB of gain, +18 dBm P1dB with a +34 dBm output IP3 at 850 MHz while requiring only 75 mA from a single positive supply. The combined dual amplifier circuit delivers up to +20 dBm P1dB with +35 dBm OIP3 for specific application bands through 4 GHz.

Parameter		Min.	Тур.	Max.	Units
	DC - 1.0 GHz	12.5	15		dB
	1.0 - 2.0 GHz	11	13		dB
Gain	2.0 - 3.0 GHz	10	12		dB
	3.0 - 4.0 GHz	9	11		dB
	4.0 - 5.0 GHz	7.5	9.5		dB
Gain Variation Over Temperature	DC - 5 GHz		0.008	0.012	dB/ °C
	DC - 1.0 GHz		12		dB
Input Return Loss	1.0 - 4.0 GHz		10		dB
	4.0 - 5.0 GHz		8		dB
	DC - 1.0 GHz		14		dB
Output Return Loss	1.0 - 2.0 GHz		10		dB
Oulput Return Loss	2.0 - 4.0 GHz		8		dB
	4.0 - 5.0 GHz		6		dB
Reverse Isolation	DC - 5 GHz		18		dB
	0.5 - 1.0 GHz	15	18		dBm
	1.0 - 2.0 GHz	13	16		dBm
Output Power for 1 dB Compression (P1dB)	2.0 - 3.0 GHz	11	14		dBm
	3.0 - 4.0 GHz	9.5	12.5		dBm
	4.0 - 5.0 GHz	8	11		авт
	0.5 - 1.0 GHz		34		dBm
Output Third Order Intercept (IP3)	1.0 - 2.5 GHz		30		dBm
(Pout= 0 dBm per tone, 1 MHz spacing)	2.5 - 4.0 GHz		25		dBm
	4.0 - 5.0 GHz		23		dBm
Noise Figure	DC - 3.0 GHz		4.0		dB
	3.0 - 5.0 GHz		5.0		dB
Supply Current (Icq)			75		mA

Electrical Specifications, Vs= 8.0 V, Rbias= 51 Ohm, T_{A} = +25° C

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Note: Data taken with broadband bias tee on device output. All specifications refer to a single amplifier.

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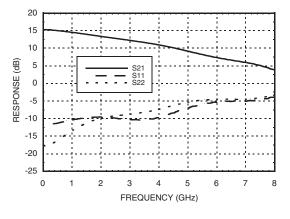
BLOCK MMIC AMPLIFIER, DC - 5 GHz

SiGe HBT DUAL CHANNEL GAIN

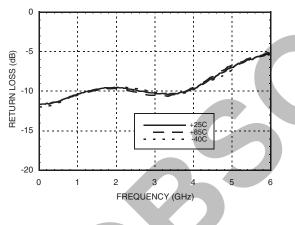
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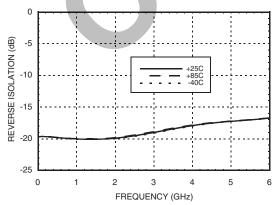
Broadband Gain & Return Loss



Input Return Loss vs. Temperature

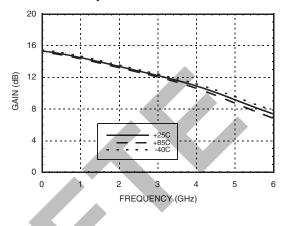


Reverse Isolation vs. Temperature

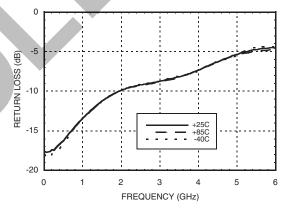


Data shown is of a single amplifier.

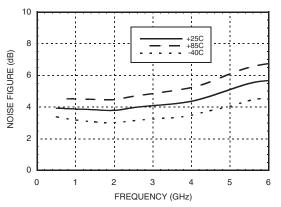
Gain vs. Temperature



Output Return Loss vs. Temperature



Noise Figure vs. Temperature



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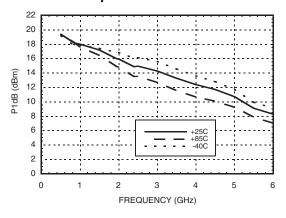
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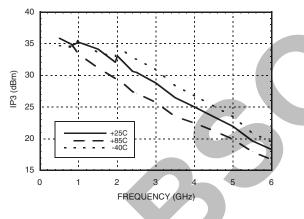
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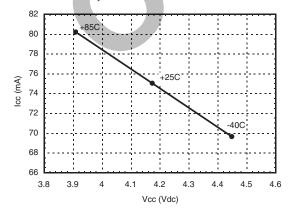
P1dB vs. Temperature



Output IP3 vs. Temperature

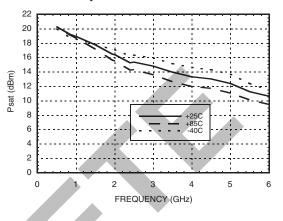


Vcc vs. Icc Over Temperature for Fixed Vs= 8V, RBIAS= 51 Ohms

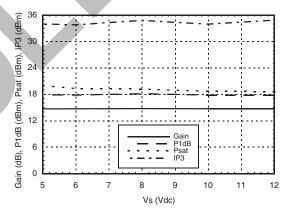


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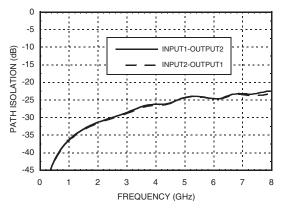
Psat vs. Temperature



Gain, Power & OIP3 vs. Supply Voltage for Constant Icc= 75 mA @ 850 MHz



Cross Channel Isolation



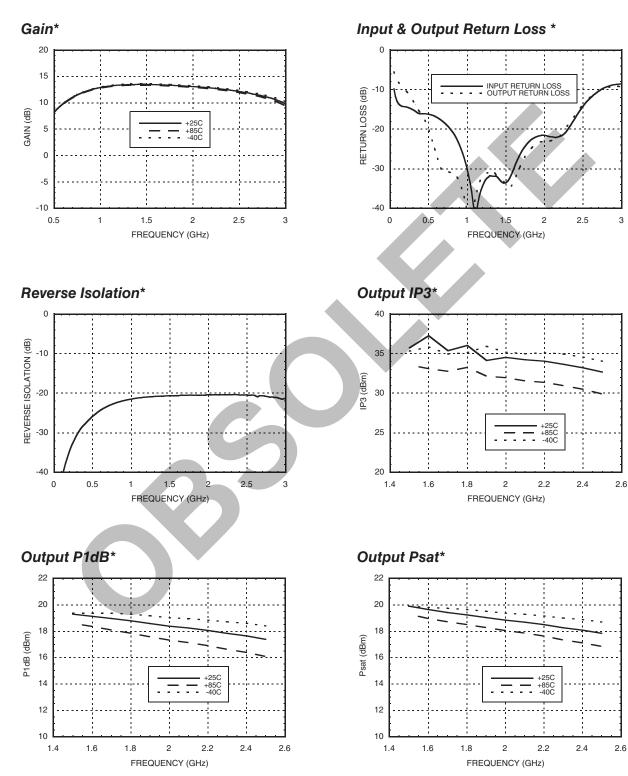
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* Measurements shown are of both channels with 1.5 - 2.5 GHz 90° splitter/combiners on input & output (see application circuit for balanced operation).

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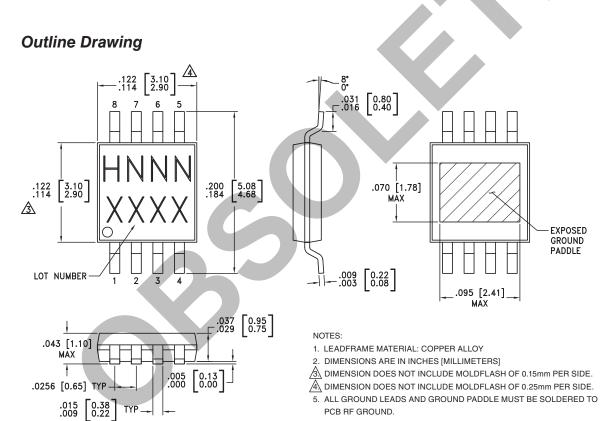


SiGe HBT DUAL CHANNEL GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+6.0 Vdc	
Collector Bias Current (Icc)	100 mA	
RF Input Power (RFIN)(Vcc = +4.2 Vdc)	+17 dBm	
Junction Temperature	150 °C	
Continuous Pdiss (T = 85 °C) (derate 29.58 mW/°C above 85 °C)	1.92 W	
Thermal Resistance (junction to ground paddle)	33.8 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	





Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC469MS8G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H469 XXXX
HMC469MS8GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>H469</u> XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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SiGe HBT DUAL CHANNEL GAIN **BLOCK MMIC AMPLIFIER, DC - 5 GHz**

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	RFIN1	This pin is DC coupled. An off chip DC blocking capacitor is required.	RFOUT1
8	RFOUT1	RF output and DC Bias (Vcc1) for the output stage.	
2, 3, 6, 7	N/C	No connection. These pins may be connected to RF ground. Performance will not be affected.	
4	RFIN2	This pin is DC coupled. An off chip DC blocking capacitor is required.	RFOUT2
5	RFOUT2	RF output and DC Bias (Vcc2) for the output stage.	
Ground Paddle	GND	Ground paddle must be connected to RF/DC ground.	

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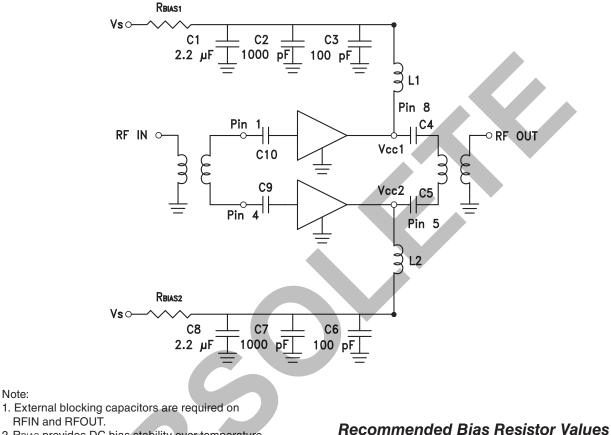


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SiGe HBT DUAL CHANNEL GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz



Application Circuit for Balanced Operation



2. RBIAS provides DC bias stability over temperature.

for lcc= 75 n	nA, RI	bias=	(Vs -	Vcc)	/ Icc
Supply Voltage	- 1/	014	01/	101/	1011

Supply Voltage (Vs)	5V	6V	8V	10V	12V
RBIAS VALUE	13 Ω	27 Ω	51 Ω	82 Ω	110 Ω
RBIAS POWER RATING	1/8 W	1/4 W	1/2 W	1/2 W	1 W

Recommended Component Values for Key Application Frequencies

Component	Frequency (MHz)						
Component	50	900	1900	2200	2400	3500	5000
L1, L2	270 nH	56 nH	18 nH	18 nH	15 nH	8.2 nH	6.8 nH
C4, C5, C9, C10	0.01 µF	100 pF					

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Evaluation PCB

HMC469MS8G / 469MS8GE

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SiGe HBT DUAL CHANNEL GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

VS1 GND J6 J5 HITTITE J3 RFIN1 **RFOUT1** J1 RFIN2 RFOUT2 J4 J2 109162 **C8** J8 .17 VS₂ GND

List of Materials for Evaluation PCB 109164^[1]

Item	Description		
J1 - J4	PCB Mount SMA Connector		
J5 - J8	DC Pins		
L1, L2	Inductor, 0402 Pkg.		
C1, C8	2.2 µF Capacitor, Tantalum		
C2, C7	1000 pF Capacitor, 0402 Pkg.		
C3, C6	100 pF Capacitor, 0402 Pkg.		
C4, C5, C9, C10	Capacitor, 0402 Pkg.		
R1, R2	Resistor, 2010 Pkg.		
U1	HMC469MS8G / HMC469MS8GE		
PCB [2]	109162 Evaluation PCB		

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

9 DRIVER & GAIN BLOCK AMPLIFIERS - SMT

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